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## NTE5700 thru NTE5705 Industrial Power Module

**Description:**

The NTE5700 through NTE5705 series of Integrated Power Circuits consist of power thyristors and power diodes configured in a single package. Applications include power supplies, control circuits and battery chargers.

**Features:**

- Glass Passivated Junctions for Greater Reliability
- Electrically Isolated Base Plate
- High Dynamic Characteristics

**Absolute Maximum Ratings:**

Maximum Repetitive Peak Reverse Voltage ( $V_S \leq 0$ ), $V_{RRM}$ .....	1200V
Maximum Non-Repetitive Peak Reverse Voltage, $V_{RSM}$ .....	1300V
Maximum Repetitive Peak Off State Voltage Gate Open Circuit, $V_{DRM}$ .....	1200V

**Thermal and Mechanical Characteristics:**

Junction Operating Temperature Range, $T_J$ .....	-40° to +125°C
Storage Temperature Range, $T_{stg}$ .....	-40° to +150°C
Maximum Internal Thermal Resistance, One Junction to Case, $R_{thJC}$	
DC Operation .....	2.24K/W
Maximum Thermal Resistance, Base to Heatsink, $R_{thCS}$	
Mounting Surface Smooth and Greased .....	0.10K/W
Mounting Torque, Base to Heatsink $\pm 10\%$ (Note 1), T .....	5Nm
Approximate Weight, wt .....	58g (2.0oz)

Note 1. A mounting compound is recommended and the torque should be checked after a period of about 3 hours to allow for the spread of the compound.

## Electrical Characteristics:

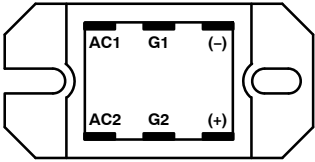
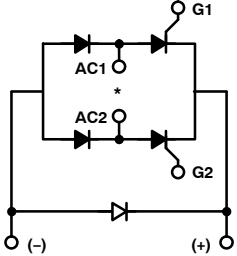
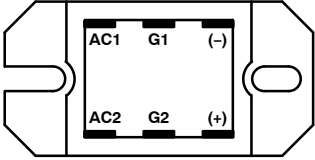
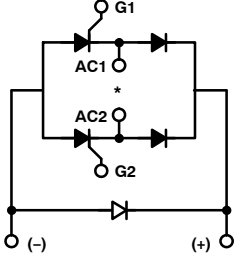
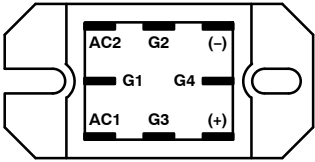
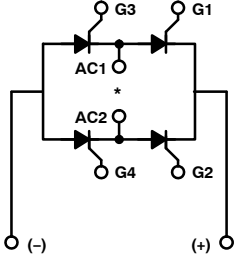
Parameter	Symbol	Test Conditions		Rating	Unit	
<b>Forward Conduction</b>						
Maximum DC Output Current	$I_O$	$T_C = +85^\circ\text{C}$ , Full Bridge Circuits (NTE5700, NTE5701, NTE5702)		25	A	
Maximum Average On-State and Forward Current	$I_{T(AV)}$ $I_{F(AV)}$	180° Sine Wave Conduction Circuits (All Types)		12.5	A	
Maximum RMS Current	$I_{RMS}$	180° Sine Wave Conduction Circuit (NTE5702)		28	A	
Maximum Peak, One-Cycle Non-Repetitive On-State or Forward Current	$I_{TSM}$ or $I_{FSM}$	10ms	100% $V_{RRM}$ Reapplied	Sinusoidal Half Wave, Initial $T_J = T_J \text{ Max}$	300	A
		8.3ms			315	A
		10ms	No Voltage Reapplied		357	A
		8.3ms			375	A
Maximum $I^2t$ for Fusing	$I^2t$	10ms	100% $V_{RRM}$ Reapplied	Initial $T_J = T_J \text{ Max}$	450	$A^2s$
		8.3ms			410	$A^2s$
		10ms	No Voltage Reapplied		637	$A^2s$
		8.3ms			580	$A^2s$
Maximum $I^2\sqrt{t}$ for Fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10ms, No Voltage Reapplied, Note 2		6365	$A^2\sqrt{s}$	
Maximum Value of Threshold Voltage	$V_{T(TO)}$	$T_J = +125^\circ\text{C}$		0.82	V	
Maximum Value of On-State Slope Resistance	$r_T$	$T_J = +125^\circ\text{C}$		12	$m\Omega$	
Maximum Peak On-State or Forward Voltage	$V_{TM}$	$I_{TM} = \pi \times I_{T(AV)}$	$T_J = +25^\circ\text{C}$ , 180° Condition	1.35	V	
	$V_{FM}$	$I_{FM} = \pi \times I_{F(AV)}$		1.35	V	
Maximum Non-Repetitive Rate of Rise of Turned On Circuit	$di/dt$	$T_J = +125^\circ\text{C}$ , from $0.67V_{DRM}$ , $I_{TM} = \pi \times I_{T(AV)}$ , $I_g = 500\text{mA}$ , $t_r < 0.5\mu\text{s}$ , $t_p > 6\mu\text{s}$		200	$A/\mu\text{s}$	
Maximum Holding Current	$I_H$	$T_J = +25^\circ\text{C}$ , Anode Supply = 6V, Resistive Load, Gate Open Circuit		100	mA	
Maximum Latching Current	$I_L$	$T_J = +25^\circ\text{C}$ , Anode Supply = 6V, Resistive Load		250	mA	
<b>Triggering</b>						
Maximum Peak Gate Power	$P_{GM}$			8.0	W	
Maximum Average Gate Power	$P_{G(AV)}$			2.0	W	
Maximum Peak Gate Current	$I_{GM}$			2.0	A	
Maximum Peak Negative Gate Voltage	$-V_{GM}$			10	V	
Maximum Gate Voltage Required to Trigger	$V_{GT}$	$T_J = -40^\circ\text{C}$		Anode Supply = 6V Resistive Load	3.0	V
		$T_J = +25^\circ\text{C}$			2.0	V
		$T_J = +125^\circ\text{C}$			1.0	V

**Electrical Characteristics (Cont'd):**

Parameter	Symbol	Test Conditions	Rating	Unit	
<b>Triggering (Cont'd)</b>					
Maximum Gate Current Required to Trigger	$I_{GT}$	$T_J = -40^\circ\text{C}$	Anode Supply = 6V Resistive Load	90	mA
		$T_J = +25^\circ\text{C}$		60	mA
		$T_J = +125^\circ\text{C}$		35	mA
Maximum Gate Voltage that will not Trigger	$V_{GD}$	$T_J = +125^\circ\text{C}$ , Rated $V_{DRM}$ Applied	0.2	V	
<b>Blocking</b>					
Maximum Critical Rate of Rise of Off-State Voltage	$dv/dt$	$T_J = +125^\circ\text{C}$ , Exponential to $0.67V_{DRM}$ , Gate Open Circuit	200	$V/\mu\text{s}$	
Maximum Peak Reverse and Off-State Leakage Current at $V_{RRM}$ , $V_{DRM}$	$I_{RM}$	$T_J = T_J \text{ Max}$ , Gate Open Circuit	10	mA	
	$I_{DM}$		2.0	mA	
RMS Isolation Voltage	$V_{INS}$	50Hz, Circuit to Base, All Terminals Shorted	2500	V	

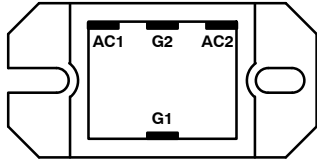
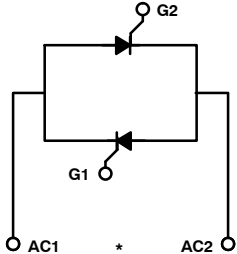
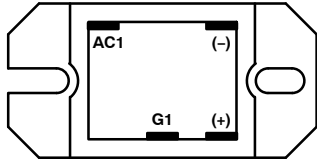

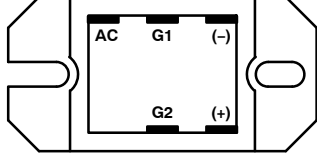
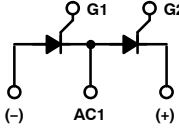
Note 2.  $I^2t$  for time  $t_x = I^2 \sqrt{t} \bullet \sqrt{t_x}$ .

**Pin Connection and Schematic Diagrams:**

NTE No.	Description	Terminal Positions	Schematic Diagrams
<b>5700</b>	Single Phase, Hybrid Bridge, Common Cathode, Freewheeling Diode		
<b>5701</b>	Single Phase, Hybrid Bridge, Common Anode, Freewheeling Diode		
<b>5702</b>	Single Phase, All SCR Bridge		

\* For transient protection, a Metal Oxide Varistor (MOV) may be connected externally across terminals AC1 & AC2.

**Pin Connection and Schematic Diagrams (Cont'd):**

NTE No.	Description	Terminal Positions	Schematic Diagrams
5703	SCR AC Switch		
5704	Hybrid Doubler		
5705	SCR Doubler		

\* For transient protection, a Metal Oxide Varistor (MOV) may be connected externally across terminals AC1 & AC2.

